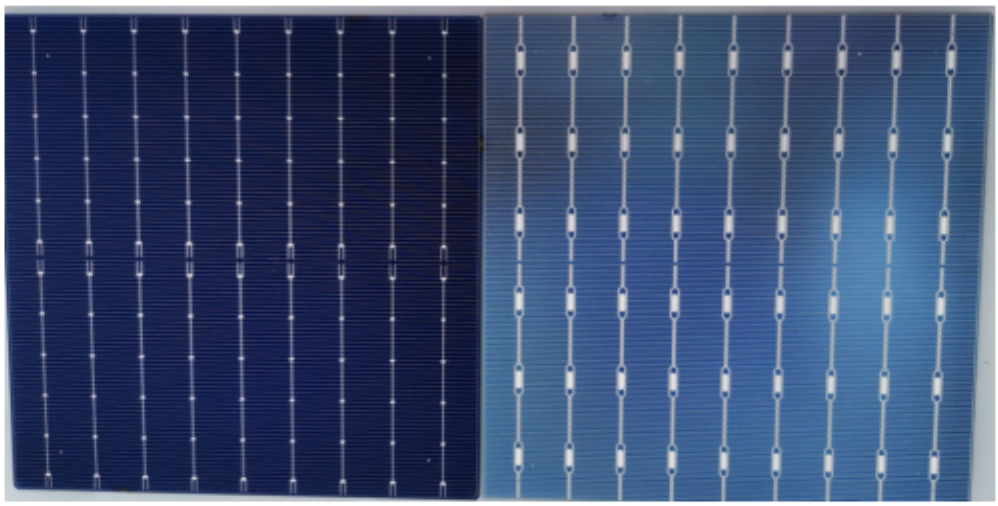
单晶 PERC 电池规格书（158.75*158.75-9BB）

1、产品名称 Product Name

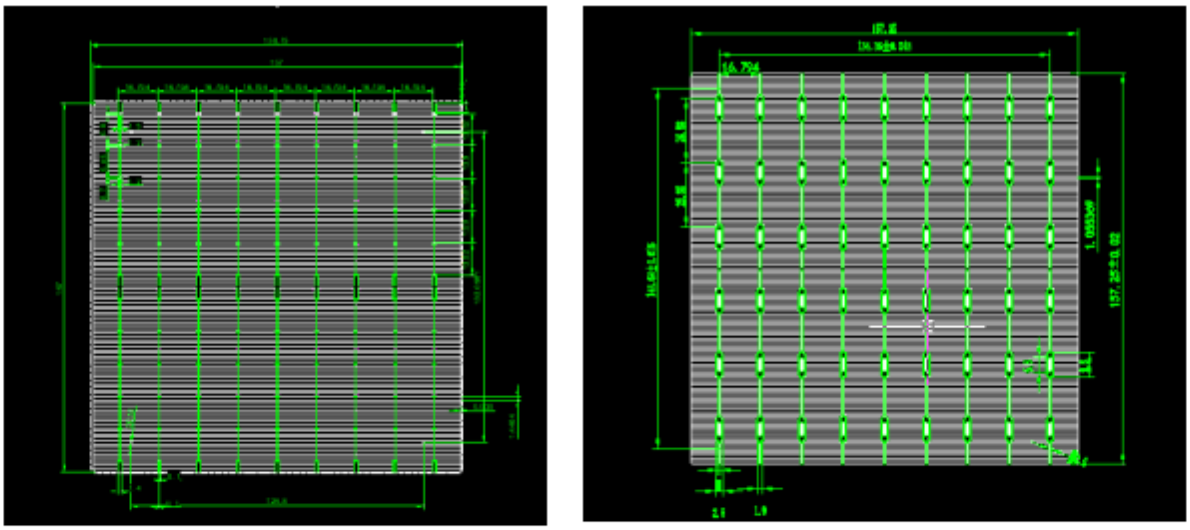
XM -M158D 9BB



2、物理特性 Physical Characteristics

尺寸 Dimension	158.75mm*158.75mm±0.25mm
厚度 Thickness	200um±20um
正面 Front（-）	二氧化硅加上氮化硅蓝色复合减反膜 (PID Free) Silicon nitride anti-reflection coating (PID Free)
	9*0.1mm 主栅线(银)，110 根副栅线 9 Bus-bar with 0.1mm width 110 fingers
背面 Rear(+)	氧化铝加氮化硅复合层；铝背场局域接触。 Aluminum oxide and silicon nitride composite layer Aluminum back field local contact
	六段式，银背电极宽度 1.9mm。 Grid Width 1.9mm 6 Sections

3、网版图纸 Cell Layout



4、电性能特性 Electrical Characteristics

Eff(%)	Pm(Wp)	Vm(V)	Im(A)	Voc(V)	Isc(A)	FF（%）
22.7	5.72	0.583	9.813	0.683	10.265	81.6
22.6	5.70	0.582	9.786	0.682	10.248	81.49
22.5	5.67	0.581	9.760	0.681	10.232	81.38
22.4	5.65	0.580	9.733	0.680	10.215	81.27
22.3	5.62	0.579	9.706	0.679	10.198	81.16
22.2	5.59	0.578	9.679	0.678	10.180	81.06
22.1	5.57	0.577	9.653	0.677	10.163	80.95
22.0	5.54	0.576	9.618	0.676	10.136	80.85
21.9	5.52	0.575	9.600	0.675	10.129	80.74
21.8	5.49	0.574	9.564	0.674	10.101	80.64
21.7	5.47	0.573	9.546	0.673	10.093	80.53
21.6	5.44	0.572	9.510	0.672	10.065	80.43
21.5	5.42	0.571	9.492	0.671	10.055	80.33
21.4	5.39	0.570	9.456	0.670	10.028	80.22

标准测试条件：光强 1000W/m^2，光谱 AM=1.5，温度 25°

Test condition : 1000 W/m^2 , AM 1.5, 25°C

逆电流：电池片在反向电压-12V 时，Irev2≤1A

Reverse characteristics: Current of cell sat reverse bias -12V，should be lower than 1A

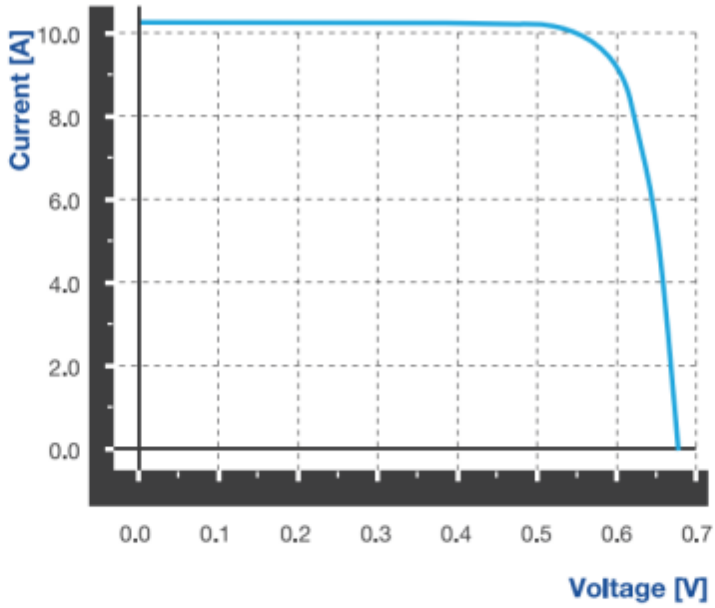
5、温度系数 Temperature coefficients

Current (%/K)	0.04
Voltage (%/K)	-0.36
Power (%/K	-0.36

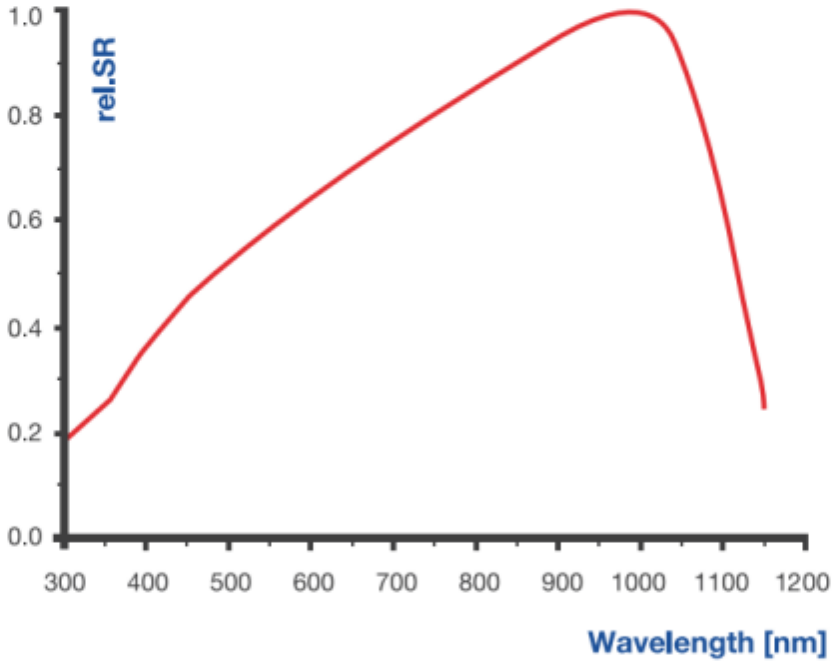
6、光衰减 LID

检验项目 Item	检验标准 Inspection method
光衰减 LID	辐照量不低于 5KWh/m^2，功率衰减≤2.5% Light intensity：1000W/m^2 Irradiation time：5 hours power attenuation ≤2.5%

7、IV 曲线 IV Curve



8、光谱响应 Spectral Response



9、优势 Product superiority

1、100%经过 EL 全检，确保出货电池片无隐裂和断栅；

Automatic EL inspection ensuring the shipment of cell without any cracks and disturbation

2、表面膜色均匀，无印刷瑕疵，外观美观；

Uniform and nice surface film without printing faults

3、低反向漏电流，PID 工艺，提高组件长期使用可靠性；

Low reverse leakage current and PID technique improving the service reliability of modules for long time

4、按照 0.1%效率一个档位分选，降低组件封装损耗。

Sorting by 0.1% efficiency etch time reducing the losses of module packaging